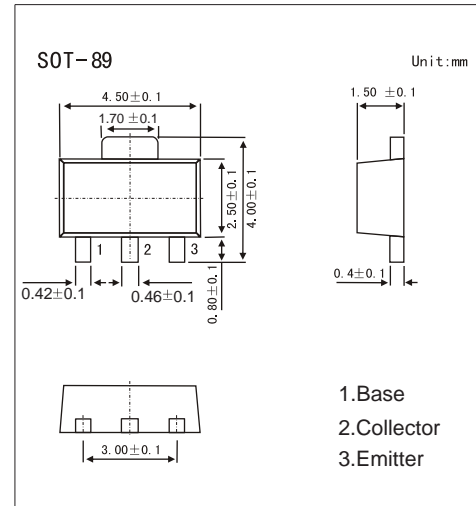


PNP Transistors

2SB1386

■ Features

- Low $V_{CE(sat)}$.
 $V_{CE(sat)} = -0.35V$ (Typ.)
($I_C/I_B = -4A / -0.1A$)
- Excellent DC current gain
- Epitaxial planar type
- PNP silicon transistor



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-30	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	I_C	-5	A
Collector current(Pulse)	I_{CP}^*	-10	A
Collector power dissipation	P_C	0.5	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

* Single pulse, $P_w=10ms$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	$I_C=-50 \mu A$	-30			V
Collector-emitter breakdown voltage	BV_{CEO}	$I_C=-1mA$	-20			V
Emitter-base breakdown voltage	BV_{EBO}	$I_E=-50 \mu A$	-6			V
Collector cutoff current	I_{CBO}	$V_{CB}=-20V$			-0.5	μA
Emitter cutoff current	I_{EBO}	$V_{EB}=-5V$			-0.5	μA
DC current transfer ratio	$V_{CE(sat)}$	$I_C=-4A, I_B=-0.1A$		-0.35	-1	V
Collector-emitter saturation voltage	h_{FE}	$V_{CE}=-2V, I_C=-0.5A$	82		390	
Transition frequency	f_T	$V_{CE}=-6V, I_E=50mA, f=30MHz$		120		MHz
Output capacitance	C_{ob}	$V_{CB}=-20V, I_E=0A, f=1MHz$		60		pF

■ h_{FE} Classification

Type	2SB1386-P	2SB1386-Q	2SB1386-R
Range	82-180	120-270	180-390
Marking	BHP*	BHQ*	BHR*

PNP Transistors

2SB1386

Typical Characteristics

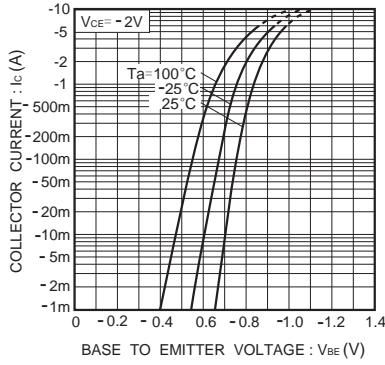


Fig.1 Grounded emitter propagation characteristics

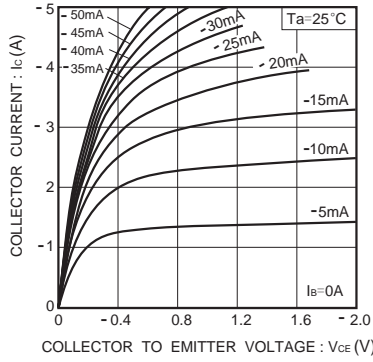


Fig.2 Grounded emitter output characteristics

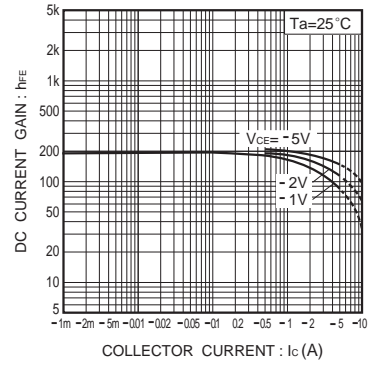


Fig.3 DC current gain vs. collector current (I)

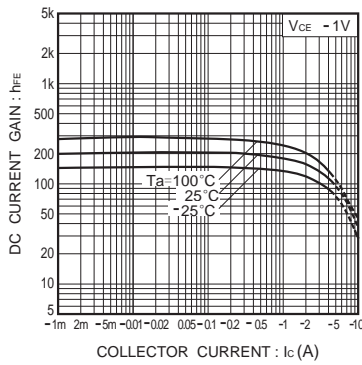


Fig.4 DC current gain vs. collector current (II)

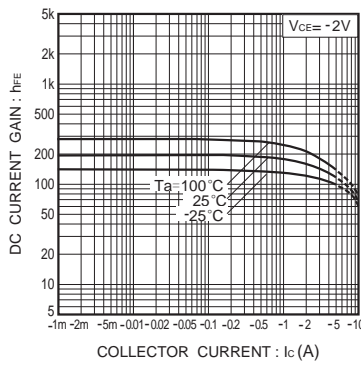


Fig.5 DC current gain vs. collector current (III)

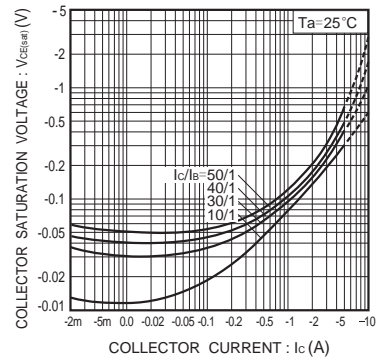


Fig.6 Collector-emitter saturation voltage vs. collector current (I)

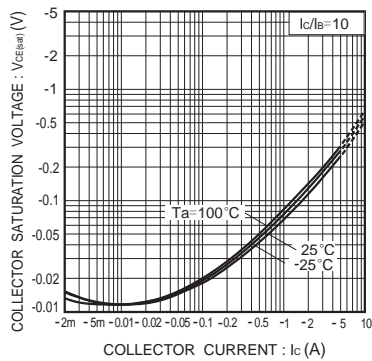


Fig.7 Collector-emitter saturation voltage vs. collector current (II)

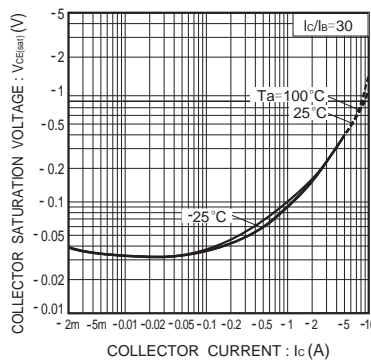


Fig.8 Collector-emitter saturation voltage vs. collector current (III)

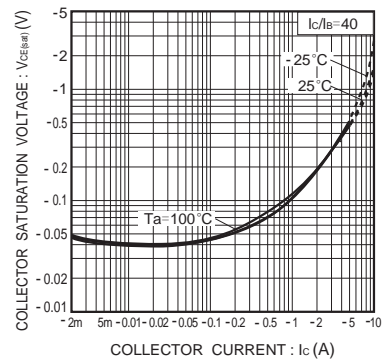


Fig.9 Collector-emitter saturation voltage vs. collector current (IV)

PNP Transistors

2SB1386

■ Typical Characteristics

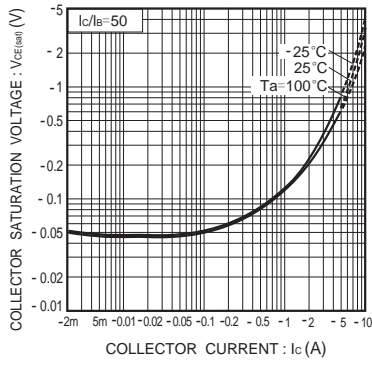


Fig.10 Collector-emitter saturation voltage vs. collector current (V)

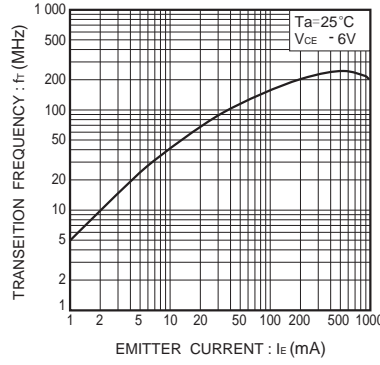


Fig.11 Gain bandwidth product vs. emitter current

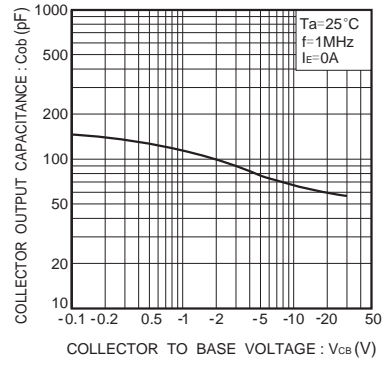


Fig.12 Collector output capacitance vs. collector-base voltage

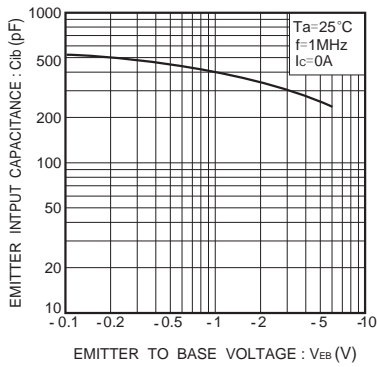


Fig.13 Emitter input capacitance vs. emitter-base voltage

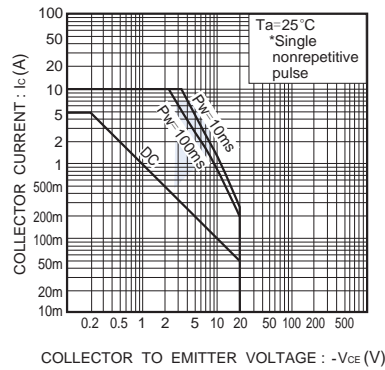


Fig.14 Safe operation area